

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Please cancel claim 27 without prejudice or disclaimer.

Please rewrite claim 1 as follows.

Listing of Claims:

Claim 1 (currently amended): A process for producing an oxide single crystal, said process comprising the steps of:

melting a raw material of said oxide single crystal in a crucible;

contacting a seed crystal to a melt of the raw material;

drawing said melt from an opening of said crucible by pulling down the seed crystal;

providing a first heater around said opening of said crucible;

growing the oxide single crystal;

providing a cooling mechanism for directly cooling said oxide single crystal while said oxide single crystal is being drawn from said opening of said crucible; and

providing a second heater around said oxide single crystal downstream from said cooling mechanism, wherein said cooling mechanism and said second heater are substantially co-linear with respect to one another along the direction in which said oxide single crystal is drawn, and a temperature gradient within a distance of 1 mm from the opening of the crucible is 100°C/mm or more.

Claim 2 (previously presented): A process for producing an oxide single crystal according to claim 1, wherein said oxide single crystal is cooled by removing ambient heat therefrom.

Claim 3 (previously presented): A process for producing an oxide single crystal according to claim 1, wherein said oxide single crystal is cooled by blowing a cooling medium thereon.

Claim 4 (previously presented): A process for producing an oxide single crystal according to claim 1, wherein said oxide single crystal is drawn from an opening of a nozzle portion provided at a tip of said crucible.

Claim 5 (original): A process for producing an oxide single crystal according to claim 3, wherein said oxide single crystal is drawn from an opening of a nozzle portion provided at a tip of said crucible.

Claim 6 (previously presented): A process for producing an oxide single crystal according to claim 1, wherein said oxide single crystal is of a planar form.

Claim 7 (original): A process for producing an oxide single crystal according to claim 3, wherein said oxide single crystal is of a planar form.

Claim 8 (original): A process for producing an oxide single crystal according to claim 4, wherein said oxide single crystal is of a planar form.

Claim 9 (original): A process for producing an oxide single crystal according to claim 5, wherein said oxide single crystal is of a planar form.

Claim 10-27 (canceled)

Claim 28 (previously presented): A process for producing an oxide single crystal according to claim 1, wherein said second heater directly heats said oxide single crystal.